Title (en)

METHOD OF PRODUCING SEMICONDUCTOR DEVICES

Publication

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Application

EP 89115504 A 19890823

Priority

DE 3828809 A 19880825

Abstract (en)

[origin: US5096844A] The invention relates to a method in particular for manufacturing bipolar transistors. By applying selective epitaxy methods and by using self-adjusting techniques, the process sequence is shortened and the transistor properties are improved.

IPC 1-7

H01L 21/82; H01L 21/285; H01L 21/20

IPC 8 full level

H01L 21/20 (2006.01); **H01L 21/285** (2006.01); **H01L 21/331** (2006.01)

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